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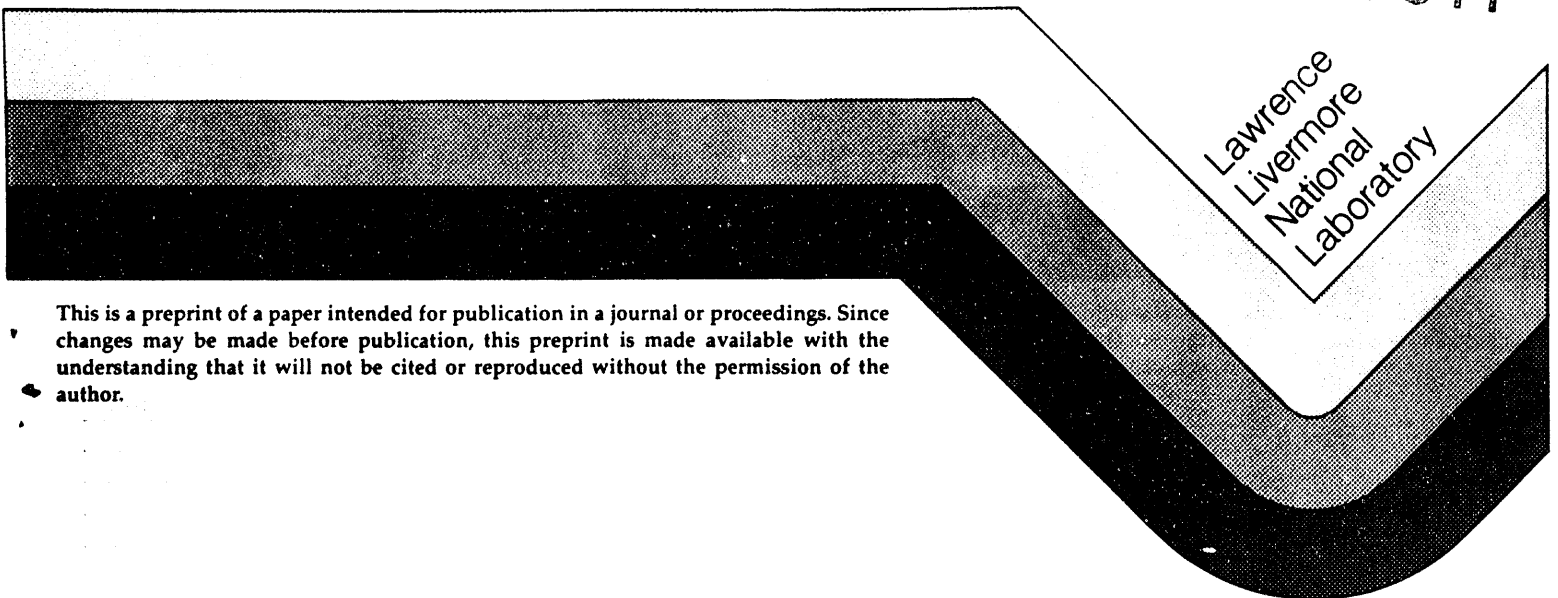
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# THE EFFECTS OF IN-SITU PROCESSING METHODS ON THE MICROSTRUCTURE AND FRACTURE TOUGHNESS OF V-V<sub>3</sub>Si COMPOSITES

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## ABSTRACT

The present paper describes ductile-phase toughening in V-V<sub>3</sub>Si in-situ composites that were produced by conventional arc melting (AM), cold-crucible induction melting (IM), and cold-crucible directional solidification (DS). Notched three-point bending tests were performed to determine the effects of synthesis method on the room temperature fracture toughness of eutectic compositions, which contain nearly equal volume fractions of V<sub>3</sub>Si and the V(Si) solid solution phase. Fracture toughness values ranged from 10 MPa√m for the AM eutectic to over 20 MPa√m for the IM and DS eutectic alloys. SEM fractography, fracture surface profiling, and chemical analyses were performed to correlate the toughness values with the microstructures and interstitial concentrations produced by the three synthesis methods.

## INTRODUCTION

Structural applications of refractory metal silicides and many other intermetallic compounds are limited by the low intrinsic fracture toughness of these materials in monolithic form. However, intermetallic ductile phase composites can possess substantially higher fracture toughness, as has been demonstrated using both artificial [1-4] and in-situ composite methods [5-7]. In-situ methods, in which a dispersed ductile phase is produced by phase separation during solidification, are especially attractive because they can minimize the cost of synthesizing the composite. However, the extent to which the microstructures can be tailored is more limited for in-situ composites than for artificial composites. Solidification conditions are a major variable through which in-situ composite microstructures can be optimized. In the present study, V-V<sub>3</sub>Si eutectic composites were synthesized by: 1) conventional arc melting (AM), 2) cold-crucible induction melting (IM), and 3) cold-crucible directional solidification (DS). The influence of casting method and crack propagation direction on the room temperature fracture toughness were measured and compared.

The V-Si system contains a number of features desirable in a model system. The phase diagram contains a eutectic between the refractory metal intermetallic V<sub>3</sub>Si and V(Si) solid solution at approximately 1870°C and contains no intermediate phases. The volume fraction of V<sub>3</sub>Si in the eutectic is predicted to be 0.51 [8]. The V and V<sub>3</sub>Si phases both have high melting points, 1910°C and 1925°C, and low densities, 6.0 g/cm<sup>3</sup> and 5.6 g/cm<sup>3</sup>, respectively. The intermetallic V<sub>3</sub>Si is an A15 compound, while V is among the most ductile of the refractory metals, with a ductile-to-brittle transition temperature below room temperature. Both the eutectic constituents exist as solid solutions within the castings, subsequently referred to as V<sub>3</sub>Si and V(Si).

## EXPERIMENTAL METHODS

Four eutectic V-V<sub>3</sub>Si alloys were prepared using three casting methods. Eutectic alloy AM-1 was arc melted using pieces of high-purity V sheet, acid cleaned in HNO<sub>3</sub>/HF solution, and vacuum degassed at 800°C for 1 h. The H concentration decreased substantially after the degassing treatment, with marginally detectable increases in N and O. The arc melted casting AM-2 and the IM and DS castings were prepared using V chips (120 ppm O, 80 ppm C, 26 ppm N, and < 3 ppm H) without acid cleaning. The silicon melting stock consisted of high-purity Si (99.999 wt.%) in all castings. The DS eutectic and IM eutectics were both produced in a segmented water-cooled copper crucible with a partially levitated melt [9]. Directional solidification was achieved using a Czochralski method in which a DS seed crystal was lowered

Strum



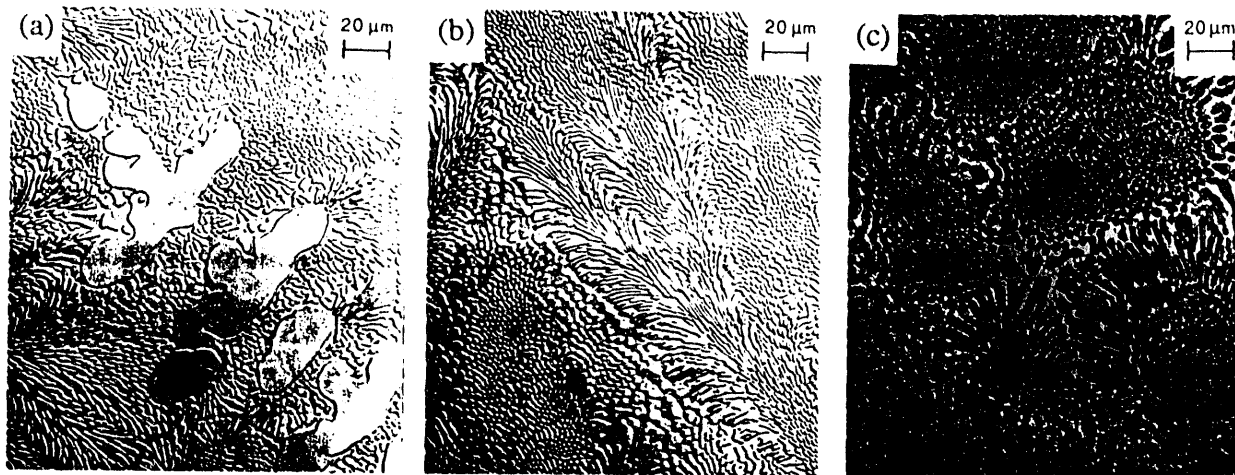


Figure 1. Typical microstructures for AM-1 (a), AM-2 (b), and IM (c) castings.

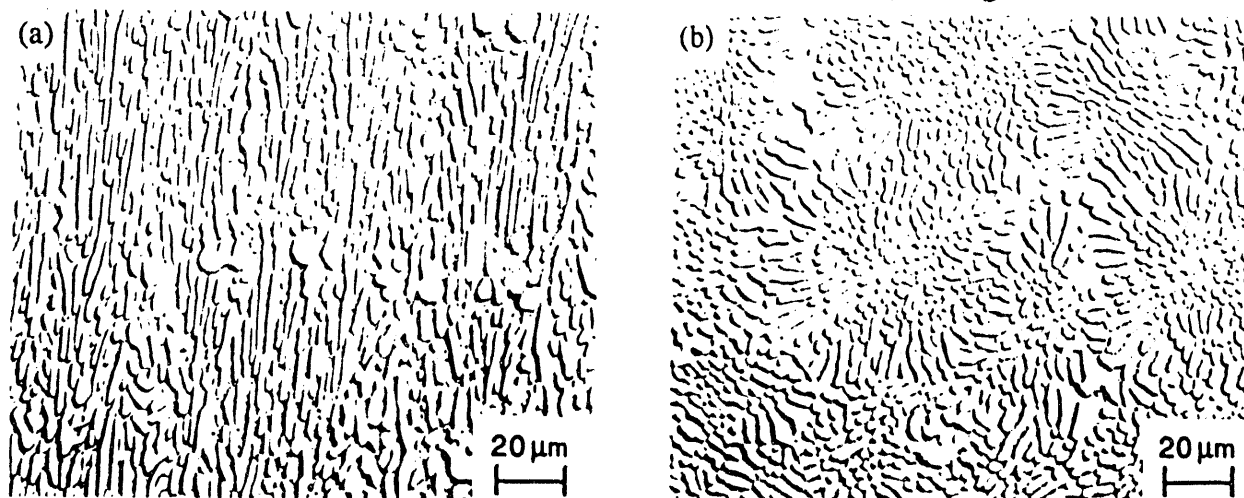


Figure 2. Typical microstructures for the directionally solidified casting in the longitudinal direction (a) and transverse direction (b).

V(Si) ligament dimensions increased with increasing rod diameter, as expected. In addition to the microstructural coarsening within the intercellular regions, occasional  $V_3Si$  dendrites were also present. These accounted for less than 1% of the casting volume except for the casting AM-1 (7.66Si), which contained approximately 2%. The AM-1 microstructure shown in Figure 1 represents the maximum amount of primary  $V_3Si$  observed.

As plotted in Figure 3, the toughness of castings AM-1 and AM-2 were similar, with average values of 10.4 and 10.6  $MPa\sqrt{m}$ , respectively. The toughness of the DS casting increased from an average of 14.4  $MPa\sqrt{m}$  for longitudinal crack propagation (DS-L) to 18.5  $MPa\sqrt{m}$  for crack propagation transverse to the crystal growth direction (DS-T). The highest average fracture toughness, 20.4  $MPa\sqrt{m}$ , was measured in the IM casting. Fracture resistance data, plotted in Figure 3a, shows the absence of any significant changes in toughness with crack propagation. The data appear evenly scattered about the average values and indicate the absence of bridging zone development with increasing crack length.

The fracture surfaces of the AM, IM, and DS castings contained mixtures of large cleavage facets and fine micro-roughened zones, as shown in Figure 4. The size of the macroscopic cleavage facets and the cleavage area fraction were both highest in the AM castings, and decreased significantly for the DS and IM castings. Macroscopic cleavage zones typically consisted of a large number of facets corresponding to individual  $V_3Si$  rods connected by smooth or stepped regions corresponding to the intervening V(Si) ligaments. The extent of V(Si) stretching in these regions was minor, as shown in Figure 5 for the AM-2 casting. Conversely, the micro-roughened zones consisted of  $V_3Si$  rods containing secondary cracks and V(Si) ligaments which display considerable plastic extension. The bright contrast at the center of the stretched ligaments clearly

Structure

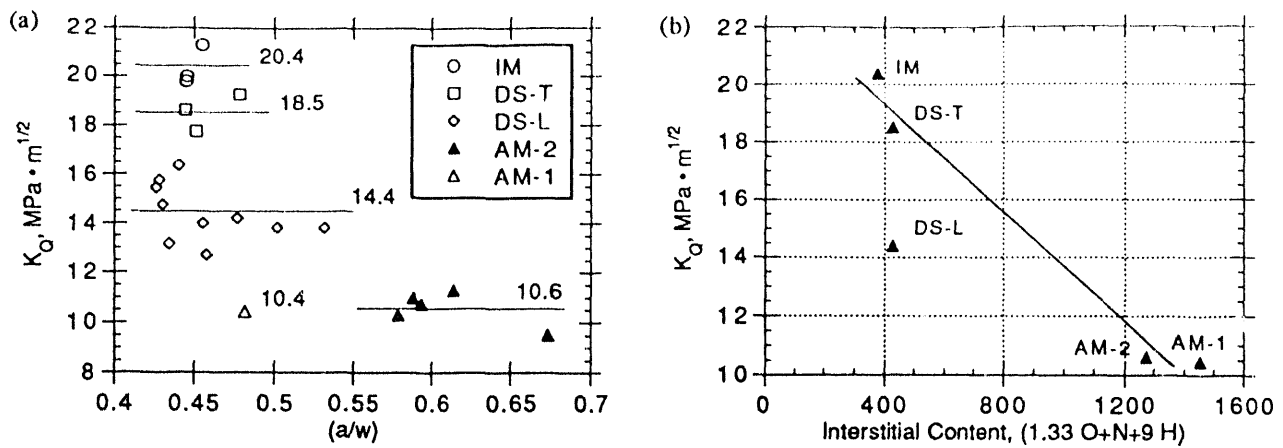


Figure 3. Fracture resistance data and average fracture toughness values for each casting (a), and fracture toughness vs. effective interstitial content (b).

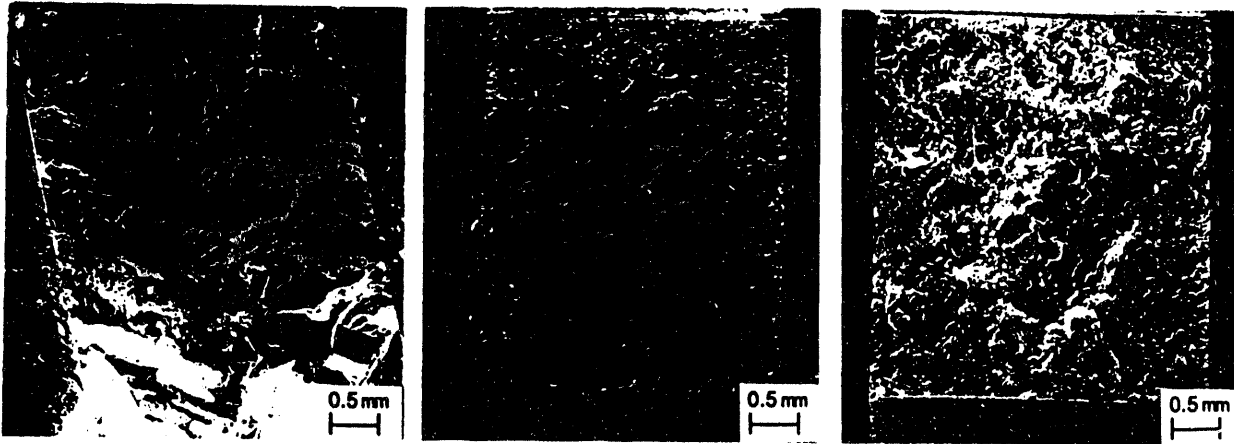


Figure 4. Fracture surfaces of, left to right, AM-2, DS-T, and IM castings.

outline each of the  $V_3Si$  rods. Similar features and contrast were observed in the IM casting.

Profiles of the fracture surfaces were prepared to quantify the magnitude of  $V(Si)$  plastic extensions beyond the  $V_3Si$  facets. However, unlike the apparently large plastic extensions viewed by SEM fractography, the presence of clearly visible  $V(Si)$  extensions was uncommon. The maximum plastic extensions measured were 0.33 to 0.66  $\mu m$  for AM-2, and 0.8 to 1.0  $\mu m$  for the DS-T specimens.

## DISCUSSION

The fracture toughness increased by a large increment for all of the eutectic composites relative to the toughness of monolithic  $V_3Si$  ( $< 1.3 \text{ MPa}\sqrt{m}$  [10]) with values from 10.4 to 20.4  $\text{MPa}\sqrt{m}$ . Decreases in Si content from 7.66 (AM-1) to 7.3 wt.% (AM-2) reduced the quantity of primary  $V_3Si$  dendrites but had no significant effect on the fracture toughness, which only increased from 10.4 to 10.6  $\text{MPa}\sqrt{m}$ . While the DS casting contained a coarser eutectic microstructure (indicative of the reduced thermal gradient and solidification rate during casting), the scale of the microstructure was similar for both the AM and IM castings, and therefore is unable to solely account for the toughness variations. The DS casting also contained a highly directional microstructure, with cells and rods strongly aligned in the growth direction within the cell cores.

The interstitial concentrations were affected by the synthesis methods, as shown in Table I, decreasing from the highest levels in the AM castings to much lower levels in the IM and DS castings. The influence of interstitial concentration on the Charpy impact toughness of pure V has been well documented [11], and the sensitivity to individual interstitial elements at room temperature was found to vary for N, O, and H in the ratio of 1 to 1.33 to 9, respectively. Assuming that this same ratio of interstitial sensitivities applies to the  $V(Si)$  ligaments, an effective



L) vs. transverse (DS-T) to the growth direction is under investigation, but may result from increased constraint in the V(Si) for the DS-L specimen. This behavior is predicted for cracks propagating parallel to the fiber (rod) direction [15] and would reduce the plastic energy dissipated during fracture.

## CONCLUSIONS

The room temperature fracture toughness of  $V_3Si$  ( $< 1.3 \text{ MPa}\sqrt{\text{m}}$ ) can be increased by in-situ ductile-phase toughening with V. A toughness of over  $20 \text{ MPa}\sqrt{\text{m}}$  has been measured for eutectic composites containing nearly equal volume fractions of  $V_3Si$  and V(Si) solid solution.

The toughness of V- $V_3Si$  in-situ eutectic composites is sensitive to the method of synthesis. Measured toughness values range from  $10 \text{ MPa}\sqrt{\text{m}}$  for AM material to over  $20 \text{ MPa}\sqrt{\text{m}}$  for IM alloys. The sensitivity of fracture toughness to synthesis method is due to the resulting differences in interstitial impurity contents and the directionality of the microstructure with respect to the direction of crack propagation. A decrease in toughness was observed in DS material oriented with the direction of crack propagation parallel to the axis of the  $V_3Si$  rods, or growth direction.

Little ductile-phase extension was observed in fractured composites, and no increase in toughness with increasing crack length ("R-curve behavior") was observed. These results suggest that fracture toughness models based on crack bridging may be unsuccessful in simulating the behavior of V- $V_3Si$  composites.

The fracture toughness decreases with increasing "effective" interstitial impurity content ( $[N]+1.33[O]+9[H]$ ) for composites with a random or transverse orientation of the crack with respect to the axis of the  $V_3Si$  rods. Fracture toughness is predicted to increase above  $20 \text{ MPa}\sqrt{\text{m}}$  for effective interstitial impurity concentrations below approximately 300 ppm.

## ACKNOWLEDGMENTS

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